

NTMD3P03R2

Power MOSFET -3.05 Amps, -30 Volts Dual P-Channel SOIC-8

Features

- High Efficiency Components in a Dual SOIC-8 Package
- High Density Power MOSFET with Low $R_{DS(on)}$
- Miniature SOIC-8 Surface Mount Package – Saves Board Space
- Diode Exhibits High Speed with Soft Recovery
- I_{DSS} Specified at Elevated Temperature
- Avalanche Energy Specified
- Mounting Information for the SOIC-8 Package is Provided
- Pb-Free Package is Available

Applications

- DC-DC Converters
- Low Voltage Motor Control
- Power Management in Portable and Battery-Powered Products, i.e.: Computers, Printers, PCMCIA Cards, Cellular & Cordless Telephones

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	-30	V
Gate-to-Source Voltage – Continuous	V_{GS}	± 20	V
Thermal Resistance – Junction-to-Ambient (Note 1) Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Continuous Drain Current @ 25°C Continuous Drain Current @ 70°C Pulsed Drain Current (Note 4)	$R_{\theta JA}$ P_D I_D I_D I_{DM}	171 0.73 -2.34 -1.87 -8.0	$^\circ\text{C/W}$ W A A A
Thermal Resistance – Junction-to-Ambient (Note 2) Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Continuous Drain Current @ 25°C Continuous Drain Current @ 70°C Pulsed Drain Current (Note 4)	$R_{\theta JA}$ P_D I_D I_D I_{DM}	100 1.25 -3.05 -2.44 -12	$^\circ\text{C/W}$ W A A A
Thermal Resistance – Junction-to-Ambient (Note 3) Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Continuous Drain Current @ 25°C Continuous Drain Current @ 70°C Pulsed Drain Current (Note 4)	$R_{\theta JA}$ P_D I_D I_D I_{DM}	62.5 2.0 -3.86 -3.1 -15	$^\circ\text{C/W}$ W A A A
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
Single Pulse Drain-to-Source Avalanche Energy – Starting $T_J = 25^\circ\text{C}$ ($V_{DD} = -30\text{ Vdc}$, $V_{GS} = -4.5\text{ Vdc}$, Peak I_L $= -7.5\text{ Apk}$, $L = 5\text{ mH}$, $R_G = 25\ \Omega$)	E_{AS}	140	mJ
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T_L	260	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

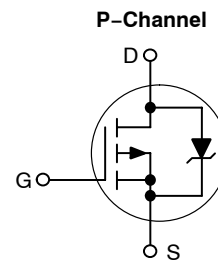
1. Minimum FR-4 or G-10 PCB, $t = \text{Steady State}$.
2. Mounted onto a 2" square FR-4 Board (1 in sq, 2 oz Cu 0.06" thick single sided), $t = \text{steady state}$.
3. Mounted onto a 2" square FR-4 Board (1 in sq, 2 oz Cu 0.06" thick single sided), $t \leq 10\text{ seconds}$.
4. Pulse Test: Pulse Width = 300 μs , Duty Cycle = 2%.



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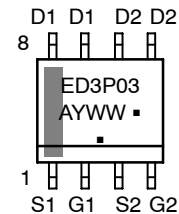
V_{DSS}	$R_{DS(ON)}$ Typ	I_D Max
-30 V	85 m Ω @ -10 V	-3.05 A



MARKING DIAGRAM* AND PIN ASSIGNMENT



SOIC-8
SUFFIX NB
CASE 751
STYLE 11



ED3P03= Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*For additional marking information, refer to Application Note AND8002/D.

ORDERING INFORMATION

Device	Package	Shipping†
NTMD3P03R2	SOIC-8	2500/Tape & Reel
NTMD3P03R2G	SOIC-8 (Pb-Free)	2500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted) (Note 5)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage (V _{GS} = 0 Vdc, I _D = -250 μAdc) Temperature Coefficient (Positive)	V _{(BR)DSS}	-30 -	- -30	- -	Vdc mV/°C
Zero Gate Voltage Drain Current (V _{DS} = -24 Vdc, V _{GS} = 0 Vdc, T _J = 25°C) (V _{DS} = -24 Vdc, V _{GS} = 0 Vdc, T _J = 125°C) (V _{DS} = -30 Vdc, V _{GS} = 0 Vdc, T _J = 25°C)	I _{DSS}	- - -	- - -	-1.0 -20 -2.0	μAdc
Gate-Body Leakage Current (V _{GS} = -20 Vdc, V _{DS} = 0 Vdc)	I _{GSS}	-	-	-100	nAdc
Gate-Body Leakage Current (V _{GS} = +20 Vdc, V _{DS} = 0 Vdc)	I _{GSS}	-	-	100	nAdc

ON CHARACTERISTICS

Gate Threshold Voltage (V _{DS} = V _{GS} , I _D = -250 μAdc) Temperature Coefficient (Negative)	V _{GS(th)}	-1.0 -	-1.7 3.6	-2.5 -	Vdc
Static Drain-to-Source On-State Resistance (V _{GS} = -10 Vdc, I _D = -3.05 Adc) (V _{GS} = -4.5 Vdc, I _D = -1.5 Adc)	R _{DS(on)}	- -	0.063 0.090	0.085 0.125	Ω
Forward Transconductance (V _{DS} = -15 Vdc, I _D = -3.05 Adc)	g _{FS}	-	5.0	-	Mhos

DYNAMIC CHARACTERISTICS

Input Capacitance	(V _{DS} = -24 Vdc, V _{GS} = 0 Vdc, f = 1.0 MHz)	C _{ISS}	-	520	750	pF
Output Capacitance		C _{OSS}	-	170	325	
Reverse Transfer Capacitance		C _{RSS}	-	70	135	

SWITCHING CHARACTERISTICS (Notes 6 and 7)

Turn-On Delay Time	(V _{DD} = -24 Vdc, I _D = -3.05 Adc, V _{GS} = -10 Vdc, R _G = 6.0 Ω)	t _{d(on)}	-	12	22	ns
Rise Time		t _r	-	16	30	
Turn-Off Delay Time		t _{d(off)}	-	45	80	
Fall Time		t _f	-	45	80	
Turn-On Delay Time	(V _{DD} = -24 Vdc, I _D = -1.5 Adc, V _{GS} = -4.5 Vdc, R _G = 6.0 Ω)	t _{d(on)}	-	16	-	ns
Rise Time		t _r	-	42	-	
Turn-Off Delay Time		t _{d(off)}	-	32	-	
Fall Time		t _f	-	35	-	
Total Gate Charge	(V _{DS} = -24 Vdc, V _{GS} = -10 Vdc, I _D = -3.05 Adc)	Q _{tot}	-	16	25	nC
Gate-Source Charge		Q _{gs}	-	2.0	-	
Gate-Drain Charge		Q _{gd}	-	4.5	-	

BODY-DRAIN DIODE RATINGS (Note 6)

Diode Forward On-Voltage	(I _S = -3.05 Adc, V _{GS} = 0 V) (I _S = -3.05 Adc, V _{GS} = 0 V, T _J = 125°C)	V _{SD}	- -	-0.96 -0.78	-1.25 -	Vdc
Reverse Recovery Time	(I _S = -3.05 Adc, V _{GS} = 0 Vdc, dI _S /dt = 100 A/μs)	t _{rr}	-	34	-	ns
		t _a	-	18	-	
		t _b	-	16	-	
Reverse Recovery Stored Charge		Q _{RR}	-	0.03	-	μC

- Handling precautions to protect against electrostatic discharge is mandatory.
- Indicates Pulse Test: Pulse Width = 300 μs max, Duty Cycle = 2%.
- Switching characteristics are independent of operating junction temperature.

TYPICAL ELECTRICAL CHARACTERISTICS

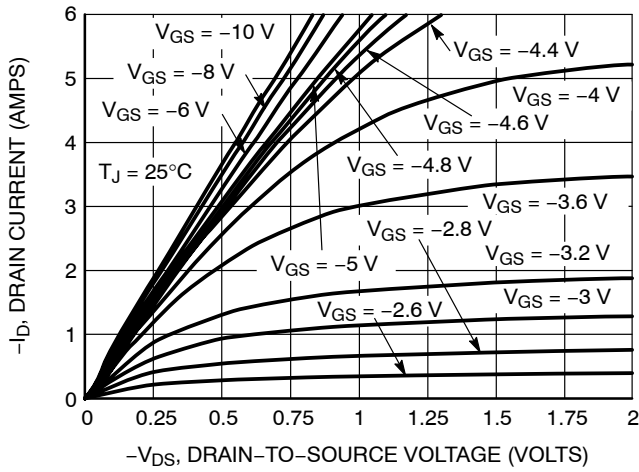


Figure 1. On-Region Characteristics

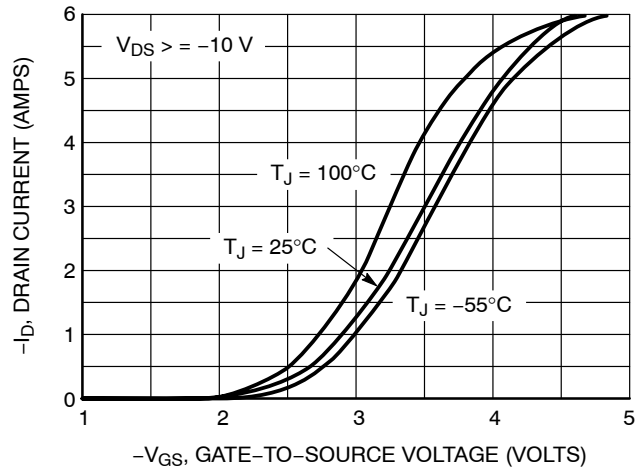


Figure 2. Transfer Characteristics

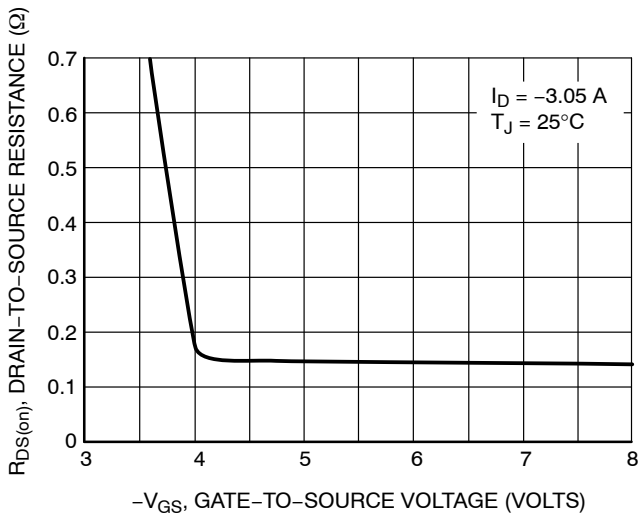


Figure 3. On-Resistance vs. Gate-to-Source Voltage

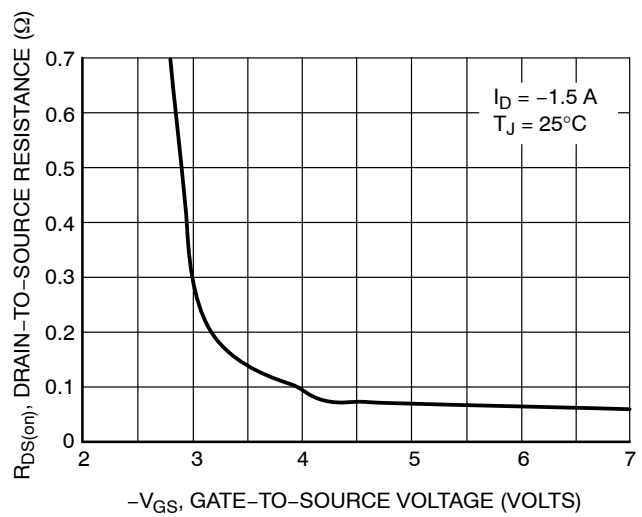


Figure 4. On-Resistance vs. Gate-to-Source Voltage

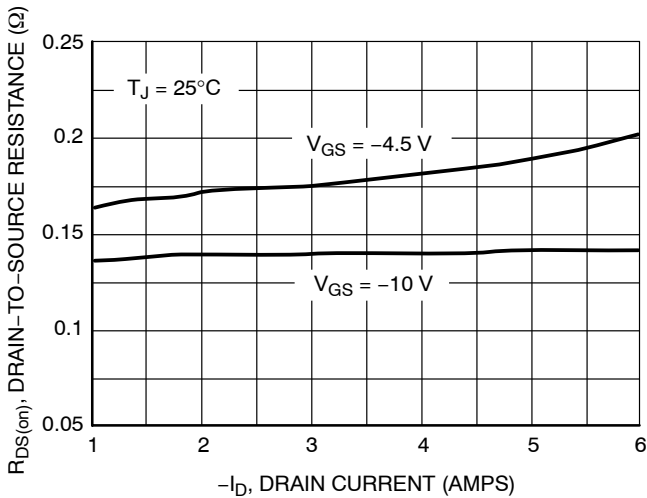


Figure 5. On-Resistance vs. Drain Current and Gate Voltage

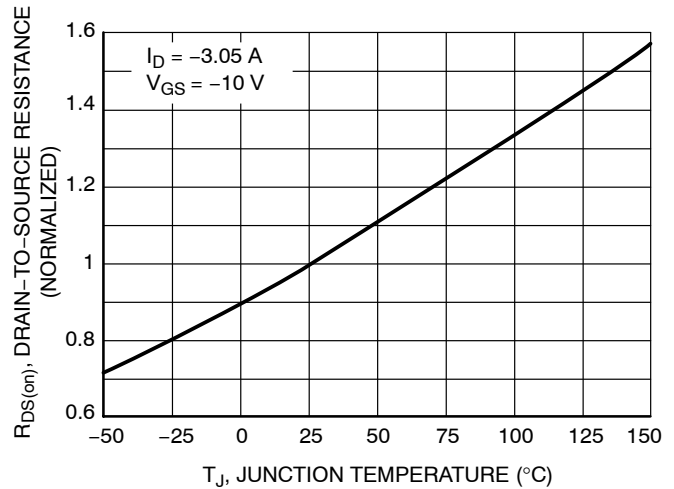


Figure 6. On Resistance Variation with Temperature

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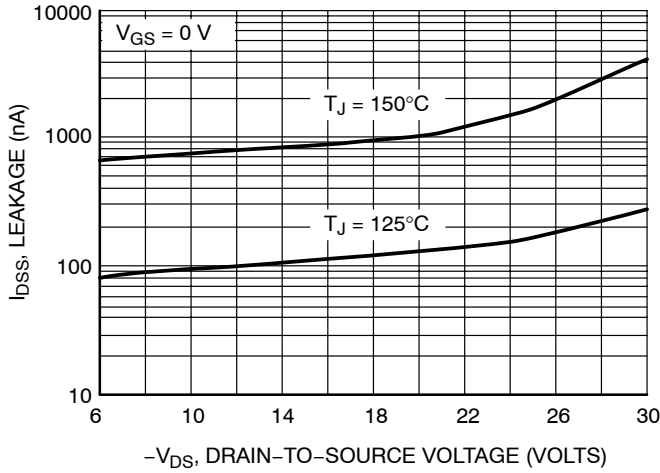


Figure 7. Drain-to-Source Leakage Current vs. Voltage

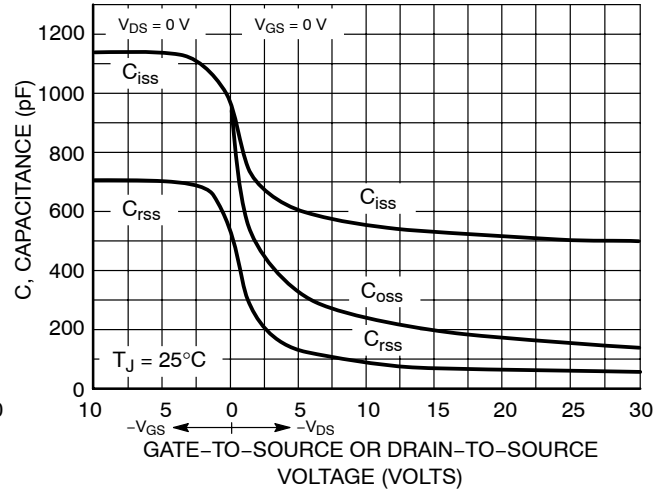


Figure 8. Capacitance Variation

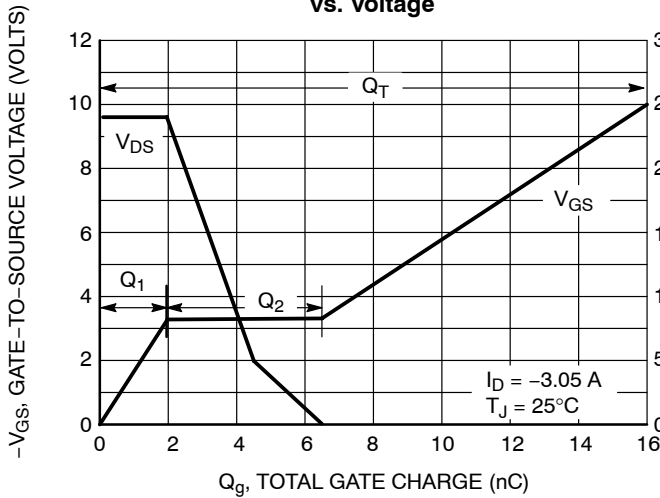


Figure 9. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

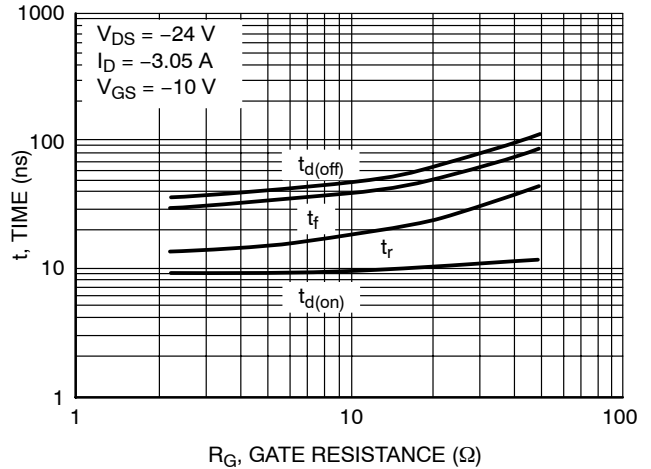


Figure 10. Resistive Switching Time Variation vs. Gate Resistance

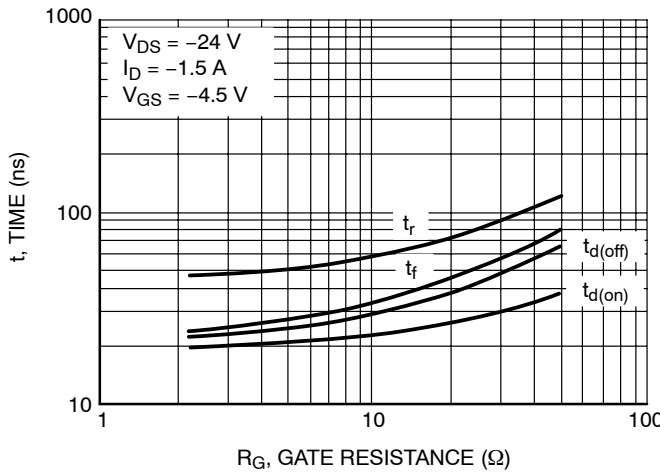


Figure 11. Resistive Switching Time Variation vs. Gate Resistance

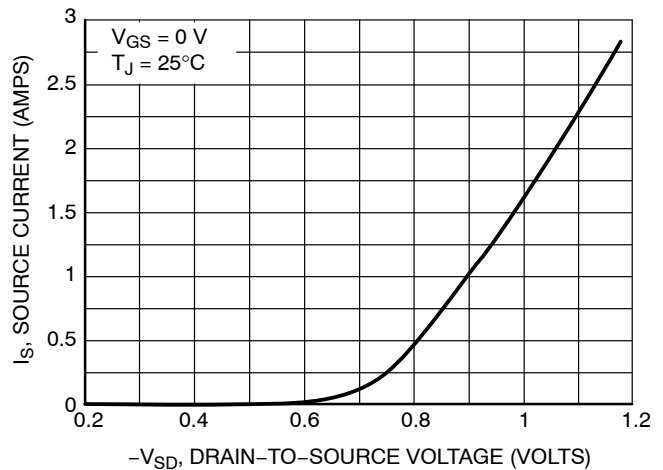


Figure 12. Diode Forward Voltage vs. Current

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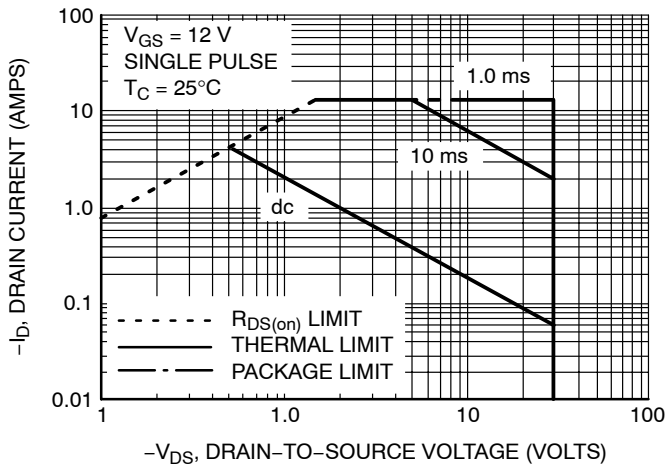


Figure 13. Maximum Rated Forward Biased Safe Operating Area

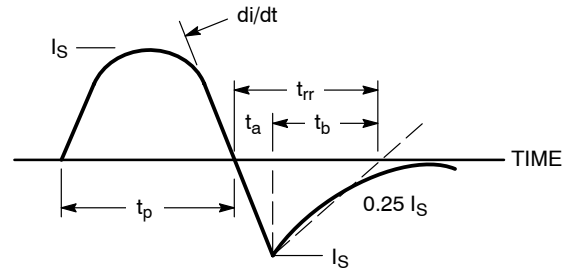


Figure 14. Diode Reverse Recovery Waveform

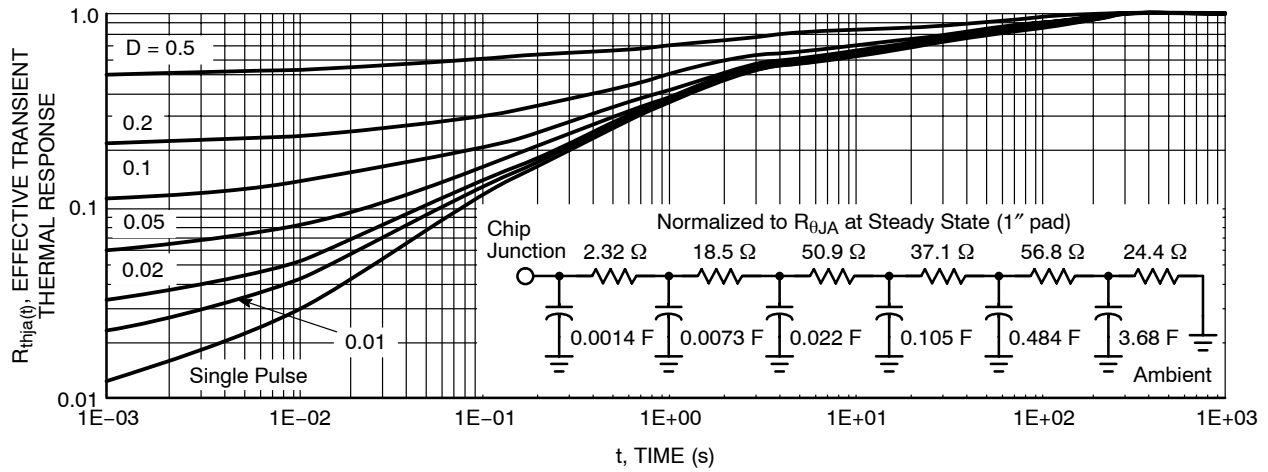
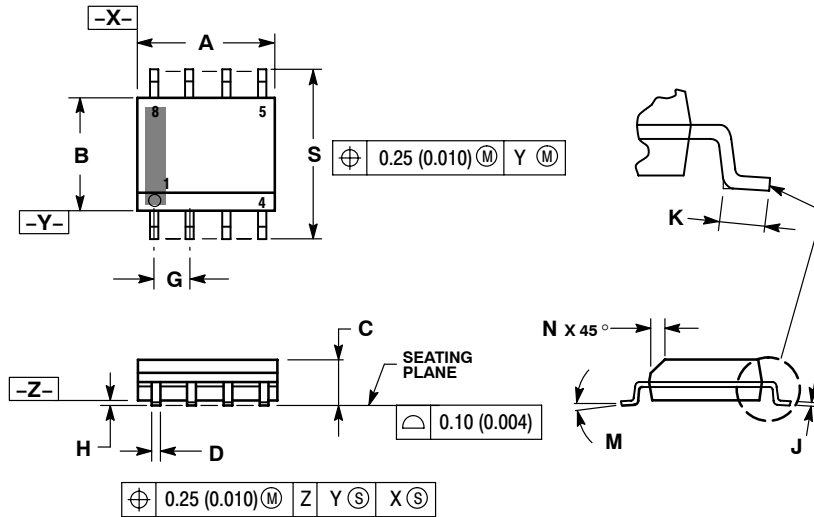


Figure 15. FET Thermal Response

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PACKAGE DIMENSIONS

SOIC-8 NB
CASE 751-07
ISSUE AG

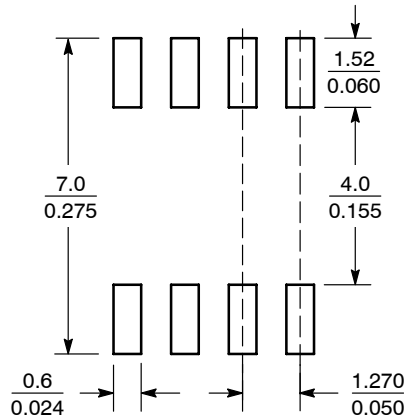


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

SOLDERING FOOTPRINT*



SCALE 6:1 (mm/inches)

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 11:

1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

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